

Switching Diodes

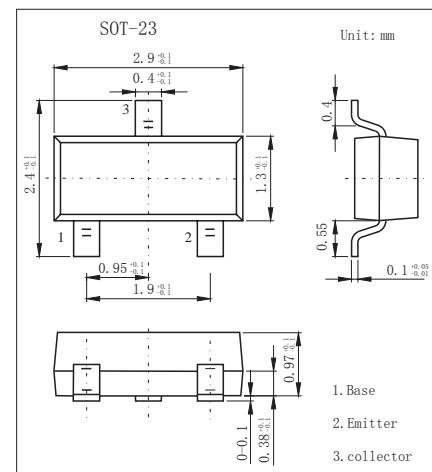
VOLTAGE RANGE: 75V
PEAK PULSE POWER:250mW

Features

- Small plastic SMD package.
- High switching sped: max.4 ns.
- Repetitive peak forward current: max.450 mA.

MECHANICAL DATA

- Case: SOT-23 Small Outline Plastic Package
- Polarity: Color band denotes cathode end
- Mounting Position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Repetitive peak reverse voltage	V _{RRM}	85	V
Continuous reverse voltage	V _R	75	V
Continuous forward current(single diode loaded *) (double diode loaded *)	I _F	215 125	mA
Repetitive peak forward current	I _{FRM}	450	mA
Non-repetitive peak forward current T _j =25 °C t=1 μ s t=1ms t=1s	I _{FSM}	4 1 0.5	A
power dissipation *	P _D	250	mW
Thermal resistance from junction to tie-point	R _{th j-to}	360	K/W
Thermal resistance from junction to ambient *	R _{th j-a}	500	K/W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

* Device mounted on an FR4 printed-circuit board.

Electrical Specification (T_A=25°C unless otherwise specified)

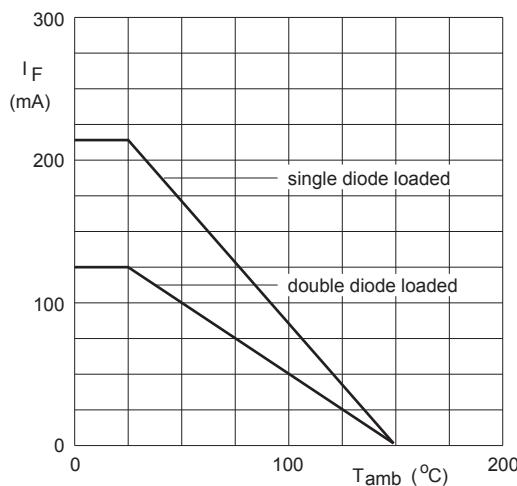
Parameter	Symbol	Test conditions	Max	Unit
Forward voltage	V _F	I _F =1 mA	715	mV
		I _F =10 mA	855	mV
		I _F =50 mA	1	V
		I _F =150 mA	1.25	V
Reverse current	I _R	V _R =75 V	1	
		V _R =25 V; T _j = 150 °C	30	μ A
		V _R =75 V; T _j = 150 °C	50	
Diode capacitance	C _d	V _R =0 V, f= 1 MHz	1.5	pF
Reverse recovery time	t _{rr}	when switched from I _F = 10 mA to I _R =10mA; R _L =100 Ω ; measured at I _R = 1mA	4	nS
Forward recovery voltage	V _{fr}	I _F = 10 mA, tr= 20 ns	1.75	V

Marking

Marking	A7
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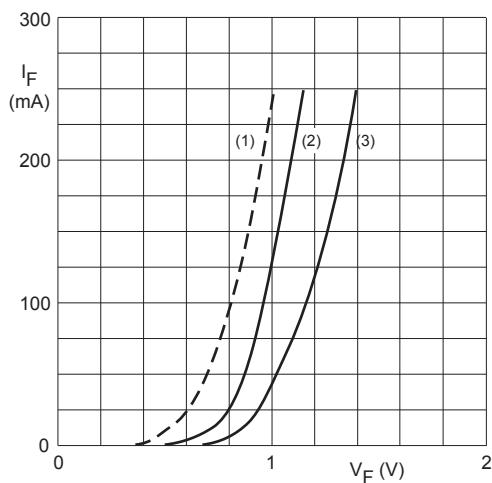
RATINGS AND CHARACTERISTIC CURVES

■ Typical Characteristics



Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) $T_j = 150$ °C; typical values.
- (2) $T_j = 25$ °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage.

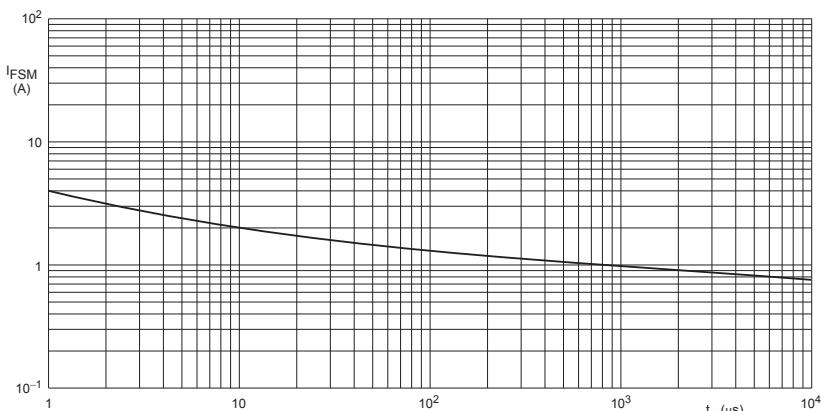


Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

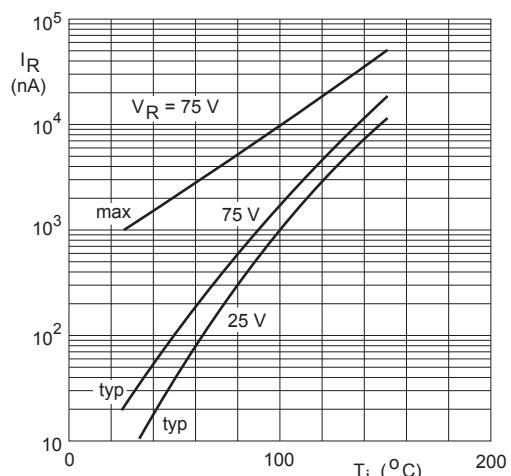


Fig.5 Reverse current as a function of junction temperature.

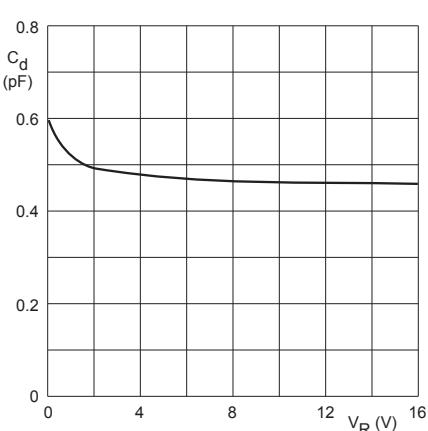


Fig.6 Diode capacitance as a function of reverse voltage; typical values.